

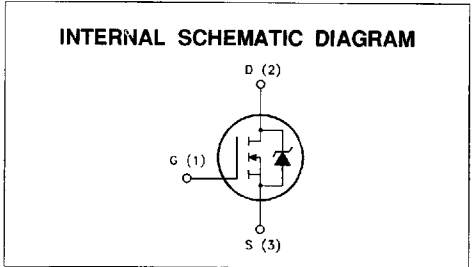
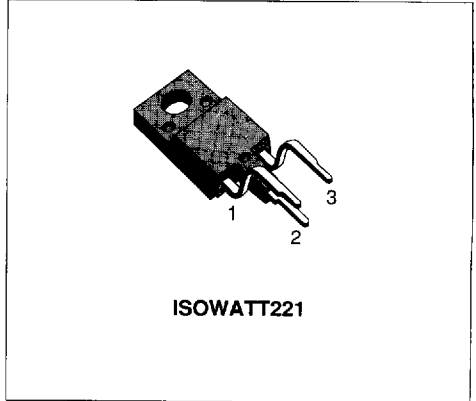
**N - CHANNEL ENHANCEMENT MODE
POWER MOS TRANSISTOR**

TYPE	V _{DSS}	R _{DS(on)}	I _D
STP3N100XI	1000 V	< 6 Ω	1.6 A

- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- LOW INPUT CAPACITANCE
- LOW GATE CHARGE
- APPLICATION ORIENTED CHARACTERIZATION

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- CONSUMER AND INDUSTRIAL LIGHTING
- DC-AC INVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLY (UPS)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	1000	V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	1000	V
V _{GS}	Gate-source Voltage	± 20	V
I _D	Drain Current (continuous) at T _c = 25 °C	1.6	A
I _D	Drain Current (continuous) at T _c = 100 °C	1	A
I _{DM} (*)	Drain Current (pulsed)	6.4	A
P _{tot}	Total Dissipation at T _c = 25 °C	30	W
	Derating Factor	0.24	W/°C
V _{ISO}	Insulation Withstand Voltage (DC)	4000	V
T _{stg}	Storage Temperature	-65 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

(*) Pulse width limited by safe operating area

THERMAL DATA

$R_{thj-case}$	Thermal Resistance Junction-case	Max	4.16	$^{\circ}C/W$
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	60	$^{\circ}C/W$
$R_{thj-amb}$	Thermal Resistance Case-sink	Typ	0.5	$^{\circ}C/W$
T_l	Maximum Lead Temperature For Soldering Purpose		300	$^{\circ}C$

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max, $\delta < 1\%$)	3	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25^{\circ}C$, $I_D = I_{AR}$, $V_{DD} = 50V$)	100	mJ
E_{AR}	Repetitive Avalanche Energy (pulse width limited by T_j max, $\delta < 1\%$)	4.5	mJ
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive ($T_c = 100^{\circ}C$, pulse width limited by T_j max, $\delta < 1\%$)	1.8	A

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250 \mu A$ $V_{GS} = 0$	1000			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating} \times 0.8$ $T_c = 125^{\circ}C$			250 1000	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 20V$			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250 \mu A$	2	3	4	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10V$ $I_D = 1.5A$ $V_{GS} = 10V$ $I_D = 1.5A$ $T_c = 100^{\circ}C$			6 12	Ω Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10V$	1.6			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs} (*)$	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 1.5A$	1	1.8		S
C_{iss}	Input Capacitance	$V_{DS} = 25V$ $f = 1MHz$ $V_{GS} = 0$		750	950	pF
C_{oss}	Output Capacitance			80	110	pF
C_{rss}	Reverse Transfer Capacitance			25	40	pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 400\text{ V}$ $I_D = 1.8\text{ A}$		70	90	ns
t_r	Rise Time	$R_G = 50\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 3)		70	90	ns
$(di/dt)_{on}$	Turn-on Current Slope	$V_{DD} = 600\text{ V}$ $I_D = 3.5\text{ A}$ $R_G = 50\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5)		100		A/ μ s
Q_g	Total Gate Charge	$V_{DD} = 400\text{ V}$ $I_D = 3.5\text{ A}$ $V_{GS} = 10\text{ V}$		48	60	nC
Q_{gs}	Gate-Source Charge			7		nC
Q_{gd}	Gate-Drain Charge			24		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 600\text{ V}$ $I_D = 3.5\text{ A}$		90	115	ns
t_f	Fall Time	$R_G = 50\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5)		60	75	ns
t_c	Cross-over Time			130	165	ns

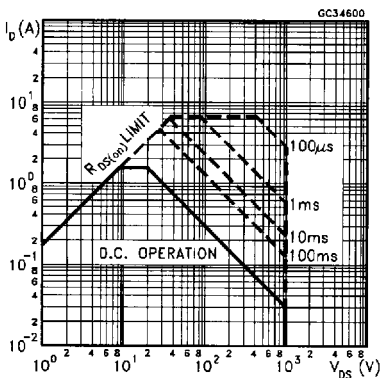
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				1.6	A
$I_{SDM}(\ast)$	Source-drain Current (pulsed)				6.4	A
$V_{SD}(\ast)$	Forward On Voltage	$I_{SD} = 1.6\text{ A}$ $V_{GS} = 0$			2	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 3.5\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$ (see test circuit, figure 5)		900		ns
Q_{rr}	Reverse Recovery Charge			10		μ C
I_{RRM}	Reverse Recovery Current			23		A

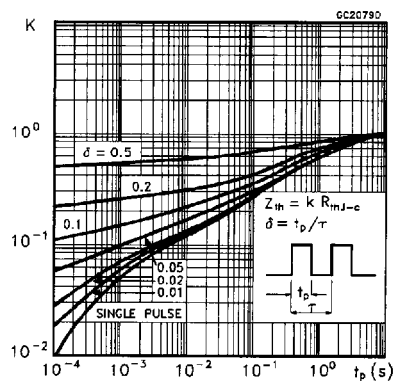
(*) Pulsed: Pulse duration = 300 μ s, duty cycle 1.5 %

(*) Pulse width limited by safe operating area

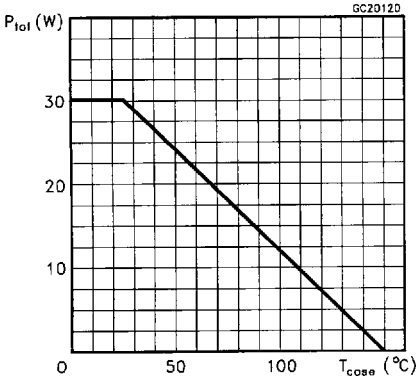
Safe Operating Area



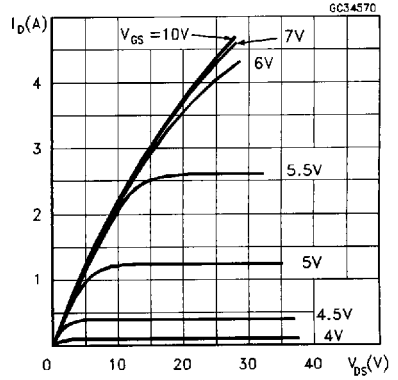
Thermal Impedance



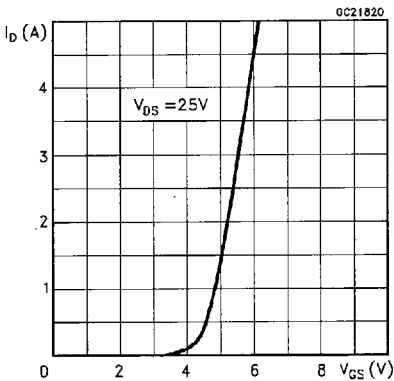
Derating Curve



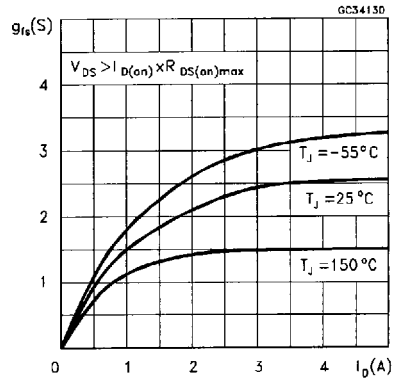
Output Characteristics



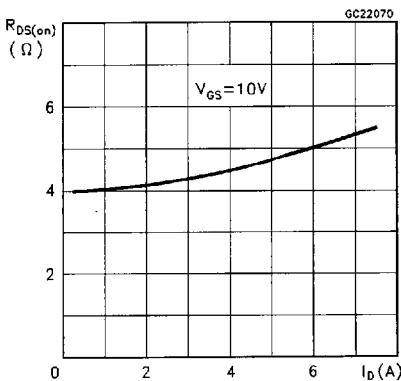
Transfer Characteristics



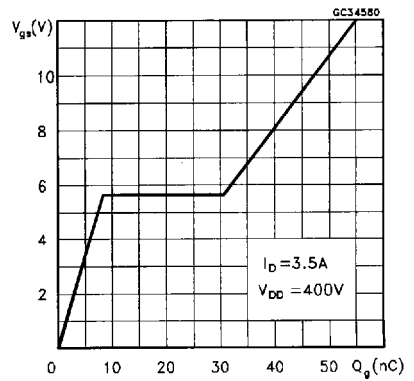
Transconductance



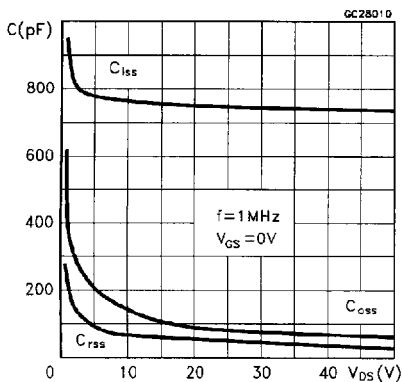
Static Drain-source On Resistance



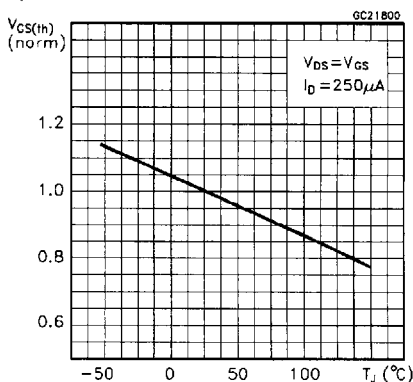
Gate Charge vs Gate-source Voltage



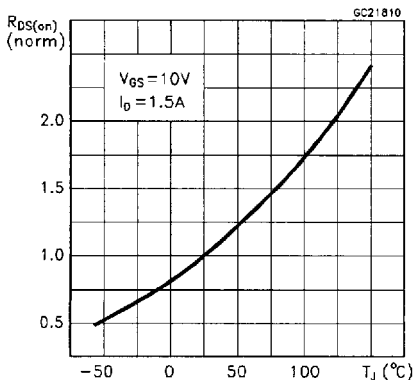
Capacitance Variations



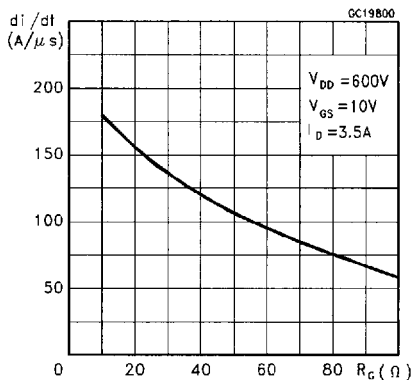
Normalized Gate Threshold Voltage vs Temperature



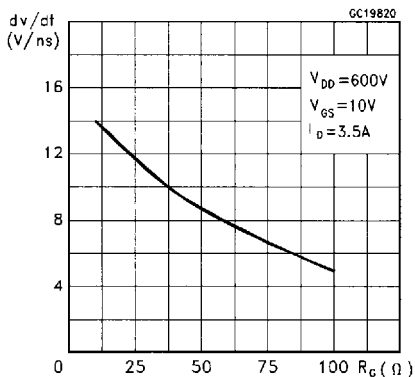
Normalized On Resistance vs Temperature



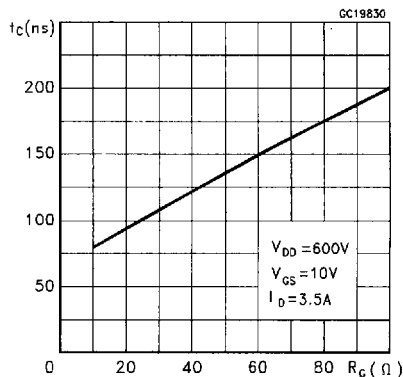
Turn-on Current Slope



Turn-off Drain-source Voltage Slope

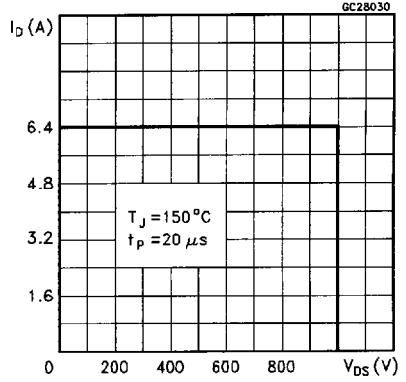
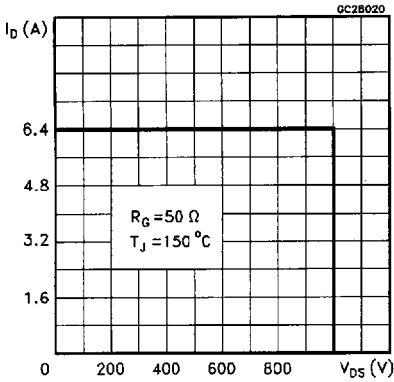


Cross-over Time



Switching Safe Operating Area

Accidental Overload Area



Source-drain Diode Forward Characteristics

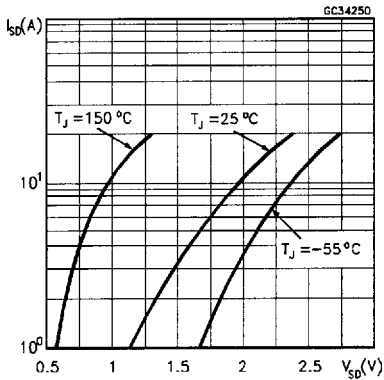


Fig. 1: Unclamped Inductive Load Test Circuits

Fig. 2: Unclamped Inductive Waveforms

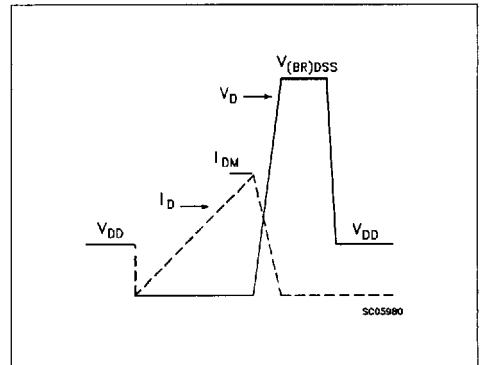
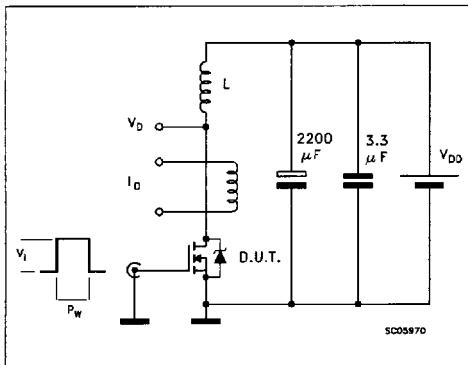


Fig. 3: Switching Times Test Circuits For Resistive Load

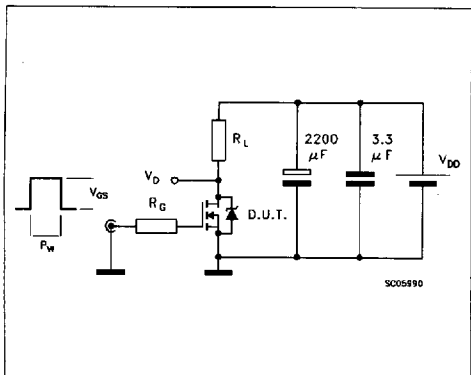


Fig. 4: Gate Charge Test Circuit

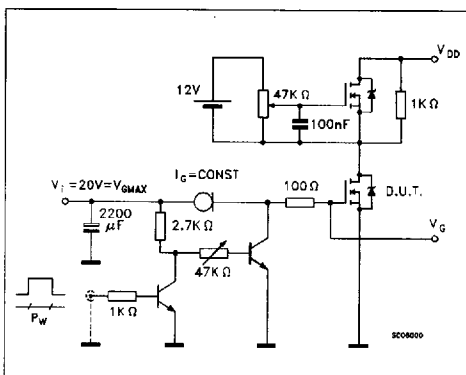


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times

